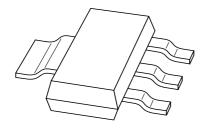
### DISCRETE SEMICONDUCTORS

# DATA SHEET



## BCP54; BCP55; BCP56 NPN medium power transistors

Product specification Supersedes data of 2001 Oct 10 2003 Feb 06





### NPN medium power transistors

### BCP54; BCP55; BCP56

#### **FEATURES**

- High collector current
- 1.3 W power dissipation.

### **APPLICATIONS**

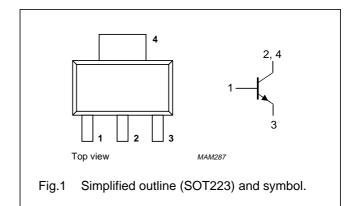
- General purpose medium power DC applications
- Low and medium frequency AC applications
- · Peripheral drivers
- Linear voltage regulators and battery chargers.

### **DESCRIPTION**

NPN medium power transistor in a SOT223 plastic package. PNP complements: BCP51, BCP52 and BCP53.

#### **PINNING**

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	80	V
I <sub>C</sub>	collector current (DC)	1	Α
I <sub>CM</sub>	peak collector current	1.5	Α

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BCP54		_	45	V
	BCP55		_	60	V
	BCP56		_	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BCP54		_	45	V
	BCP55		_	60	V
	BCP56		_	80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	1	Α
I <sub>CM</sub>	peak collector current		_	1.5	А
I <sub>BM</sub>	peak base current		_	0.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.33	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### Note

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	94	K/W
R <sub>th j-s</sub>	thermal resistance from junction to soldering point		13	K/W

### Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

<sup>1.</sup> Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

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### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	_	_	100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V; T <sub>j</sub> = 125 °C	_	_	10	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	_	_	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 5 mA; V <sub>CE</sub> = 2 V	63	_	_	
		I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 2 V	63	_	250	
		I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 2 V	40	_	_	
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 2 V		_		
	BCP54-10; BCP55-10; BCP56-10		63	_	160	
	BCP54-16; BCP55-16; BCP56-16		100	_	250	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 50 mA	_	_	500	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 0.5 A; V <sub>CE</sub> = 2 V	_	_	1	٧
f <sub>T</sub>	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	_	130	_	MHz
h <sub>FE1</sub> h <sub>FE2</sub>	DC current gain ratio of the complementary pairs	I <sub>C</sub>   = 150 mA;   V <sub>CE</sub>   = 2 V	_	_	1.6	

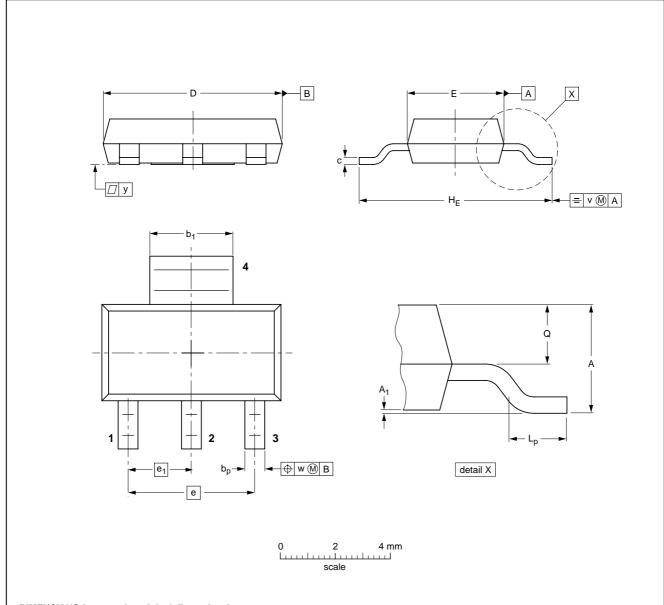
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### **PACKAGE OUTLINE**

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



### **DIMENSIONS** (mm are the original dimensions)

ι	JNIT	A	A <sub>1</sub>	bp	b <sub>1</sub>	C	D	E	е	e <sub>1</sub>	HE	Lp	Q	٧	w	у
	mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223			SC-73			<del>97-02-28</del> 99-09-13

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LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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**NOTES** 

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